



isc Silicon NPN Power Transistors

DESCRIPTION

- Low Collector Saturation Voltage
 - : V_{CE(sat)}= 0.4V(Max)@ I_C= 3A
- · Large Current Capacity
- Complement to Type 2SB920L
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

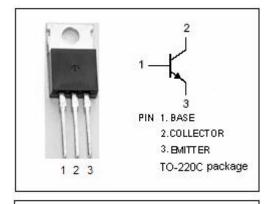
APPLICATIONS

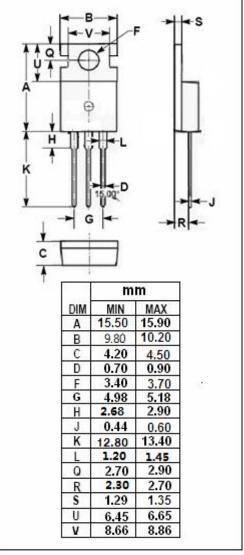


• Designed for relay drivers, high-speed inverters, converters, and other general high-current switching applications.

ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

| SYMBOL | PARAMETER | VALUE | UNIT | |
|------------------|---|-------|--------------|--|
| V _{СВО} | Collector-Base Voltage | 90 | V | |
| Vceo | Collector-Emitter Voltage | 80 | V | |
| V _{EBO} | Emitter-Base Voltage | 6 | V | |
| I _C | Collector Current-Continuous | 5 | Α | |
| I _{CP} | Collector Current-Pulse 9 | | Α | |
| P _C | Collector Power Dissipation @ T _a =25℃ | 1.75 | W | |
| | Collector Power Dissipation @ T _C =25℃ | 30 | VV | |
| TJ | Junction Temperature | 150 | $^{\circ}$ C | |
| Tstg | Storage Temperature Range -55 | | $^{\circ}$ | |







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2SD1236L

ELECTRICAL CHARACTERISTICS

Tc=25℃ unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | TYP. | MAX | UNIT | |
|----------------------|--------------------------------------|---|-----|------|-----|------|--|
| V _{(BR)CEO} | Collector-Emitter Breakdown Voltage | I _C = 1mA; R _{BE} = ∞ | 80 | | | V | |
| V _{(BR)CBO} | Collector-Base Breakdown Voltage | I _C = 1mA; I _E = 0 | 90 | | | V | |
| V _{(BR)EBO} | Emitter-Base Breakdown Voltage | I _E = 1mA; I _C = 0 | 6 | | | V | |
| V _{CE(sat)} | Collector-Emitter Saturation Voltage | I _C = 3A; I _B = 0.3A | | | 0.4 | V | |
| I _{CBO} | Collector Cutoff Current | V _{CB} = 80V; I _E = 0 | | | 100 | μА | |
| I _{EBO} | Emitter Cutoff Current | V _{EB} = 4V; I _C = 0 | | | 100 | μА | |
| h _{FE-1} | DC Current Gain | I _C = 1A; V _{CE} = 2V | 70 | | 280 | | |
| h _{FE-2} | DC Current Gain | I _C = 3A; V _{CE} = 2V | 30 | | | | |
| f _T | Current-Gain—Bandwidth Product | I _C = 1A; V _{CE} = 5V | | 20 | | MHz | |
| Switching times | | | | | | | |
| t _{on} | Turn-on Time | | | 0.1 | | μS | |
| t _{stg} | Storage Time | I _C = 2A; I _{B1} = I _{B2} = 0.2A R _L = 25 Ω; P _W =20 μ s; V _{CC} = 50V | | 1.2 | | μS | |
| tf | Fall Time | | | 0.4 | | μS | |

♦ h_{FE-1} Classifications

| Q | R | S |
|--------|---------|---------|
| 70-140 | 100-200 | 140-280 |

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